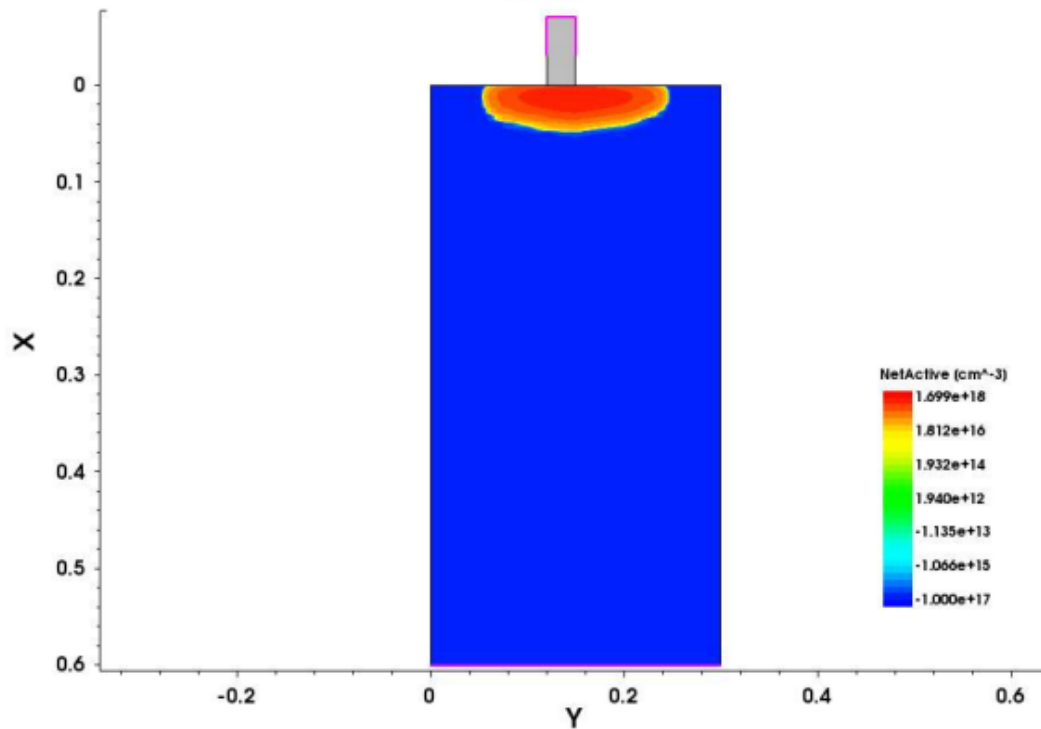


Q.1: You need to make a pn junction in sprocess with the structure roughly as shown below:



You need to use Boron for p type substrate and then implant P for getting n region. The dose and energy should be adjusted to get a peak concentration close to  $1e18 \text{ cm}^{-3}$  and a junction depth of 50 nm.

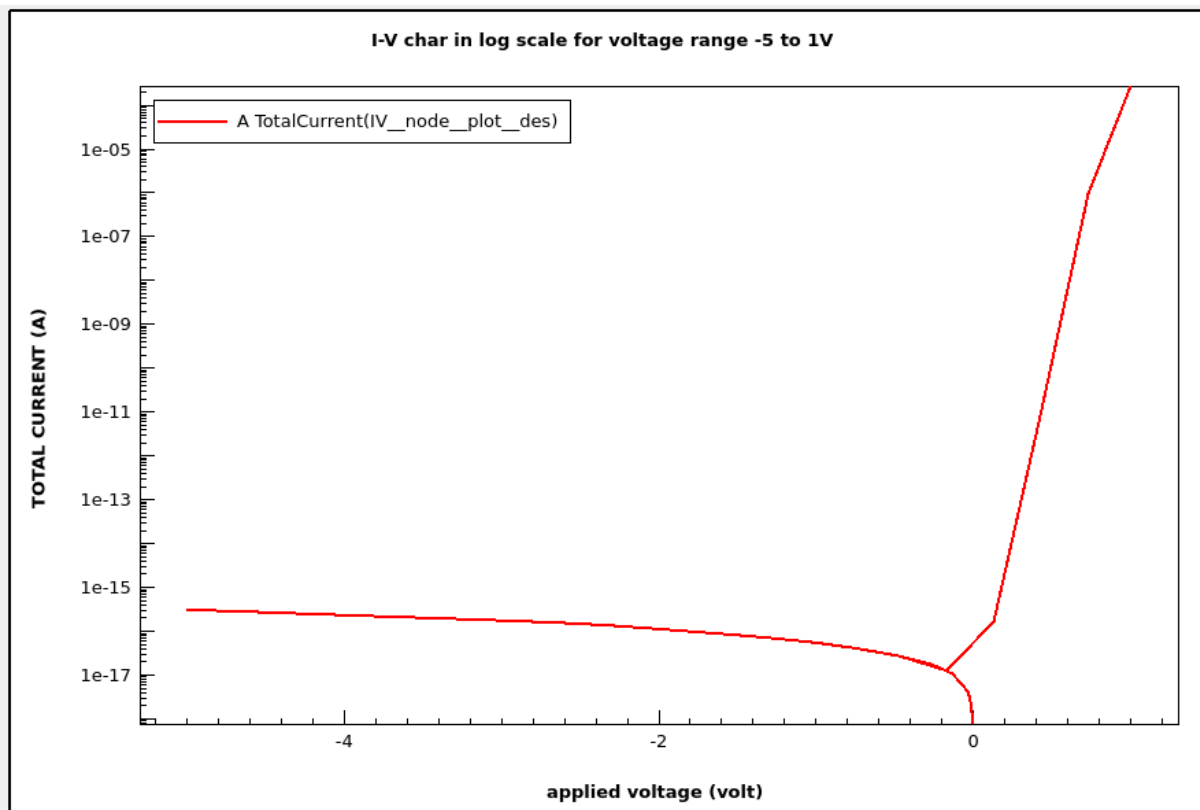
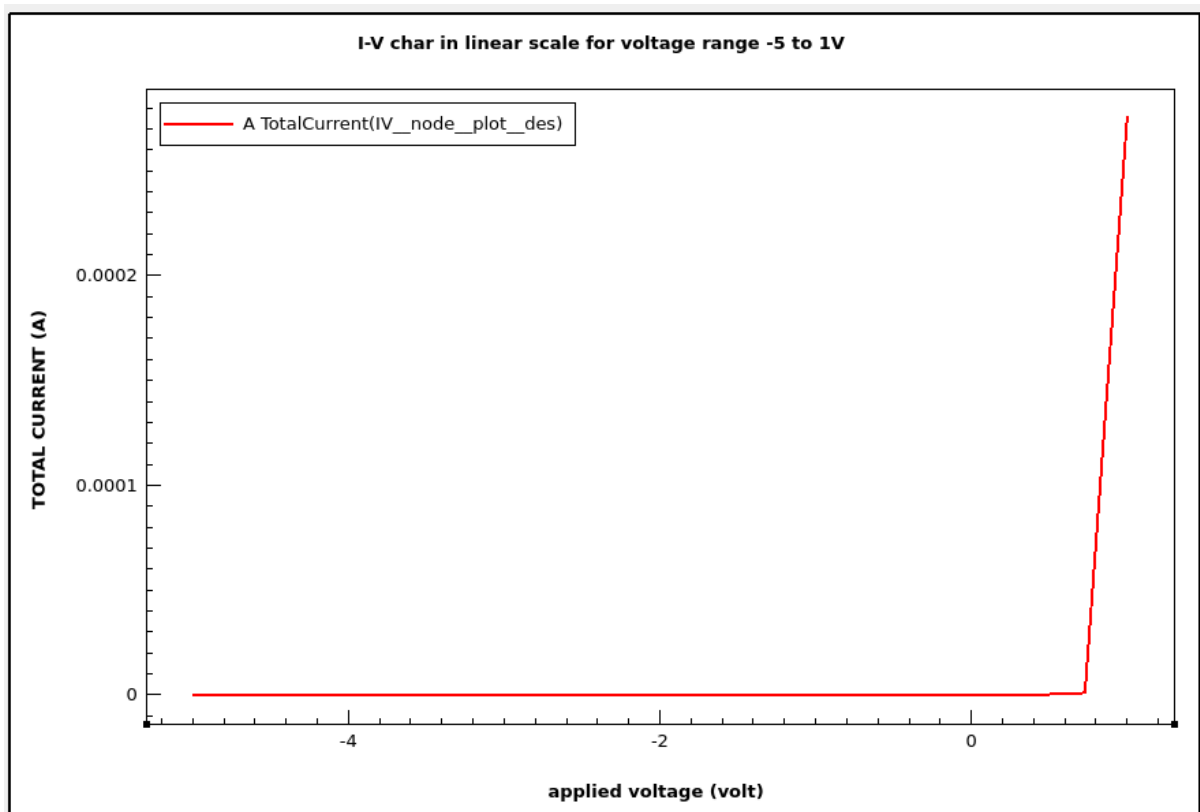
Plot the IV characteristics of the device for a voltage range of -5 V to 1 V in the linear as well as log scale. Plot the energy band diagrams, carrier concentrations and electron and hole components of the currents for different voltages, namely -1 V, 0 V, 0.2 V and 1 V.

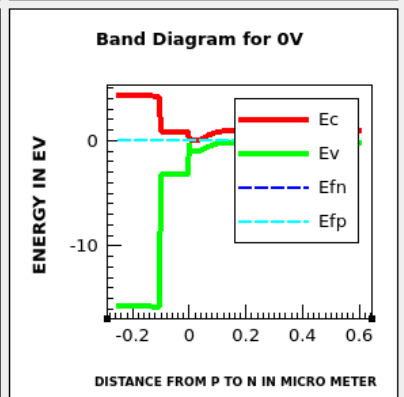
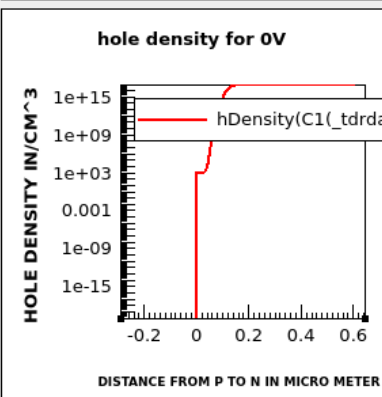
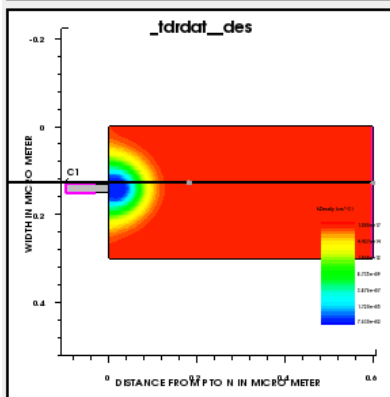
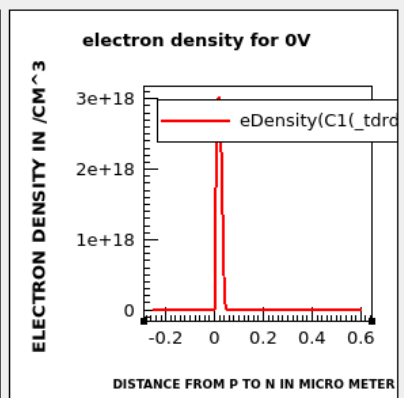
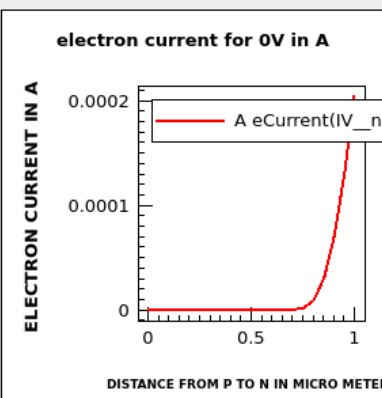
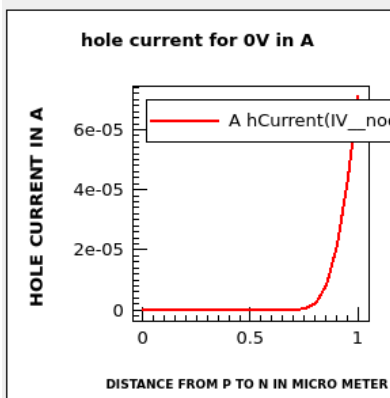
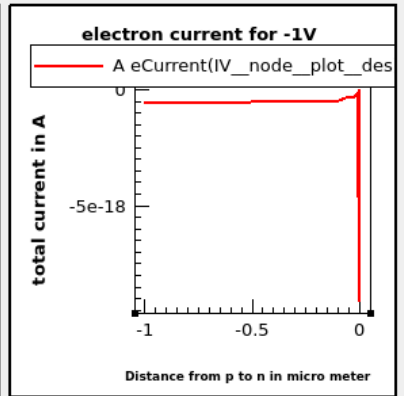
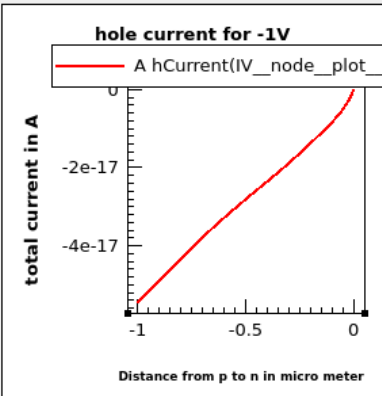
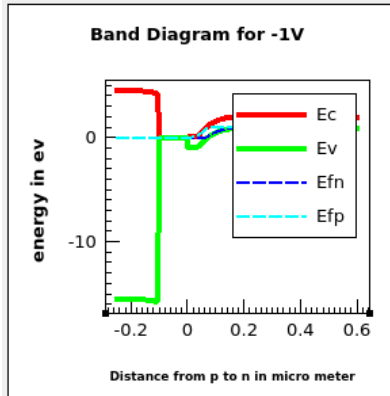
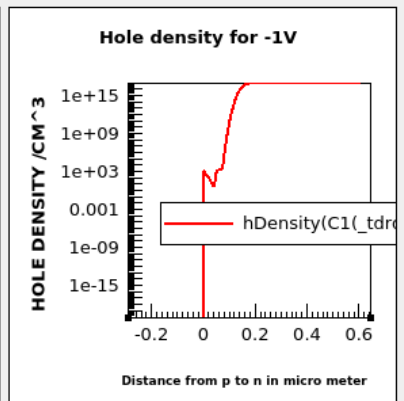
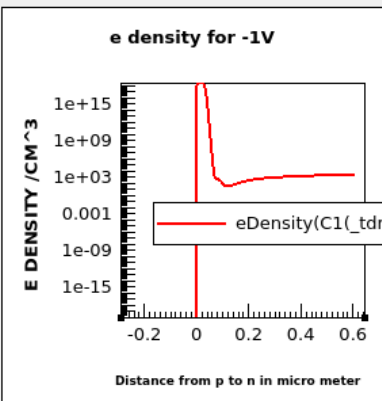
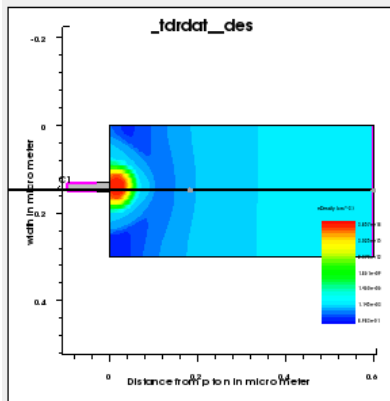
Note the reverse saturation current, compare it with what you expect theoretically? Note the slope of  $\log(I)$  vs V in different regions in forward bias and compare it with what you expect theoretically. Plot the CV characteristics in reverse bias for 0 to -10 V, use a low frequency of 1 KHz. Also plot  $1/C^2$

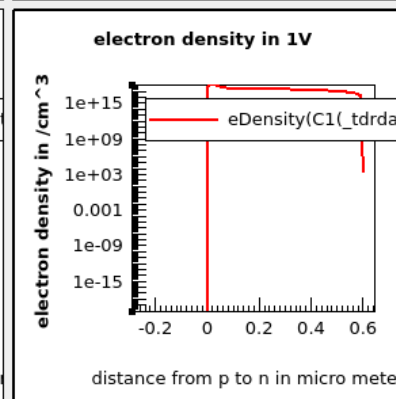
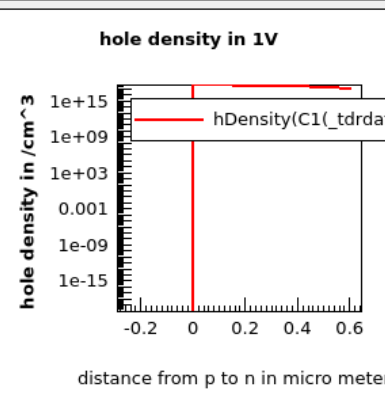
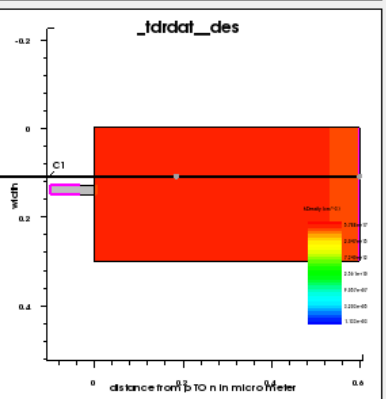
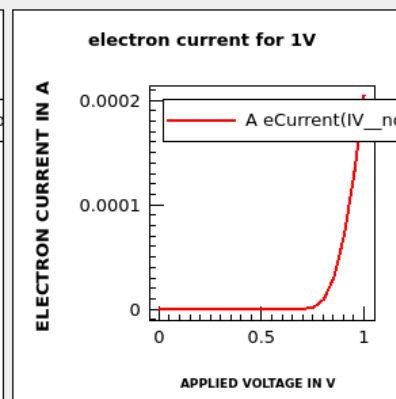
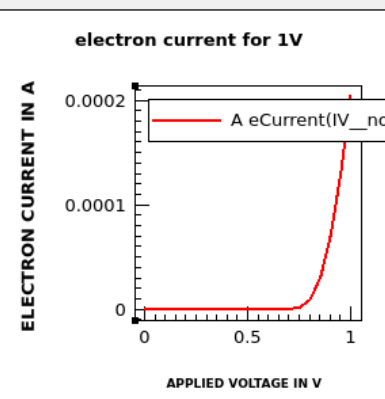
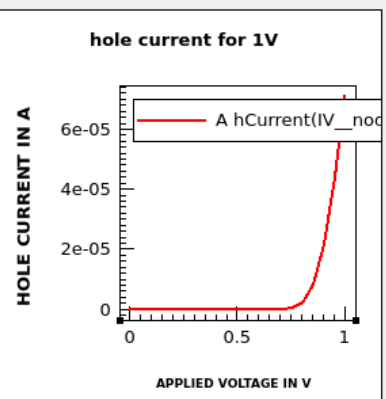
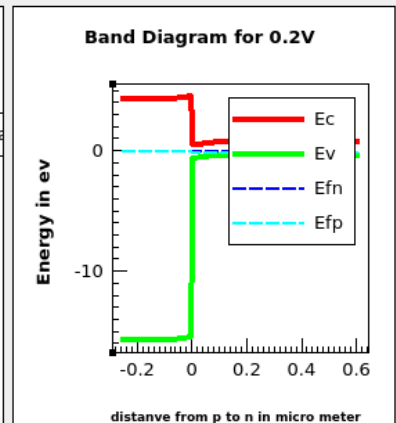
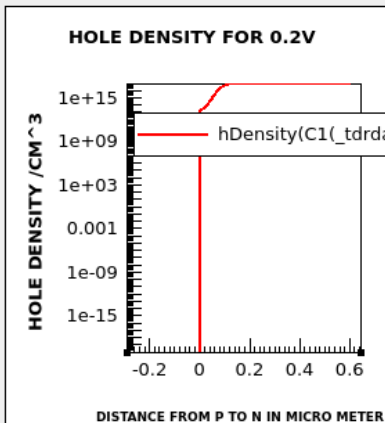
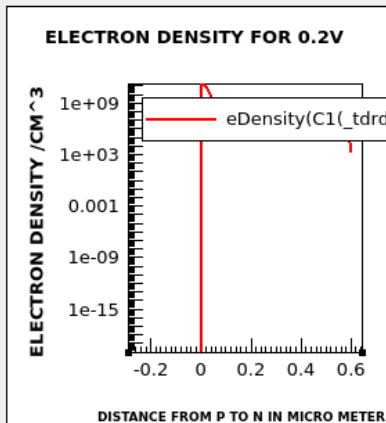
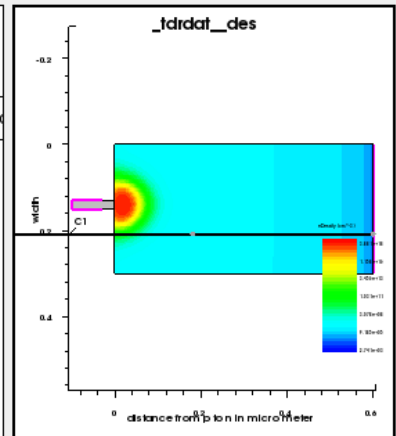
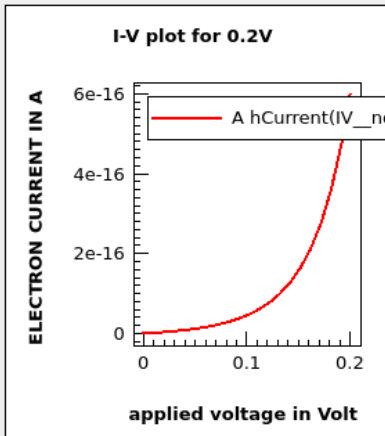
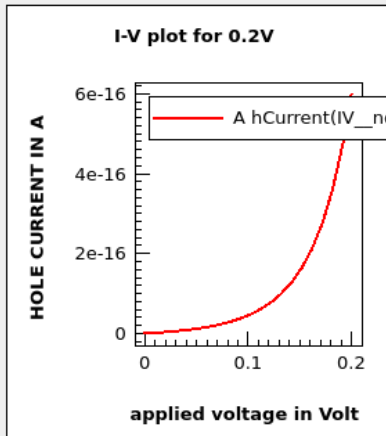
vs V and

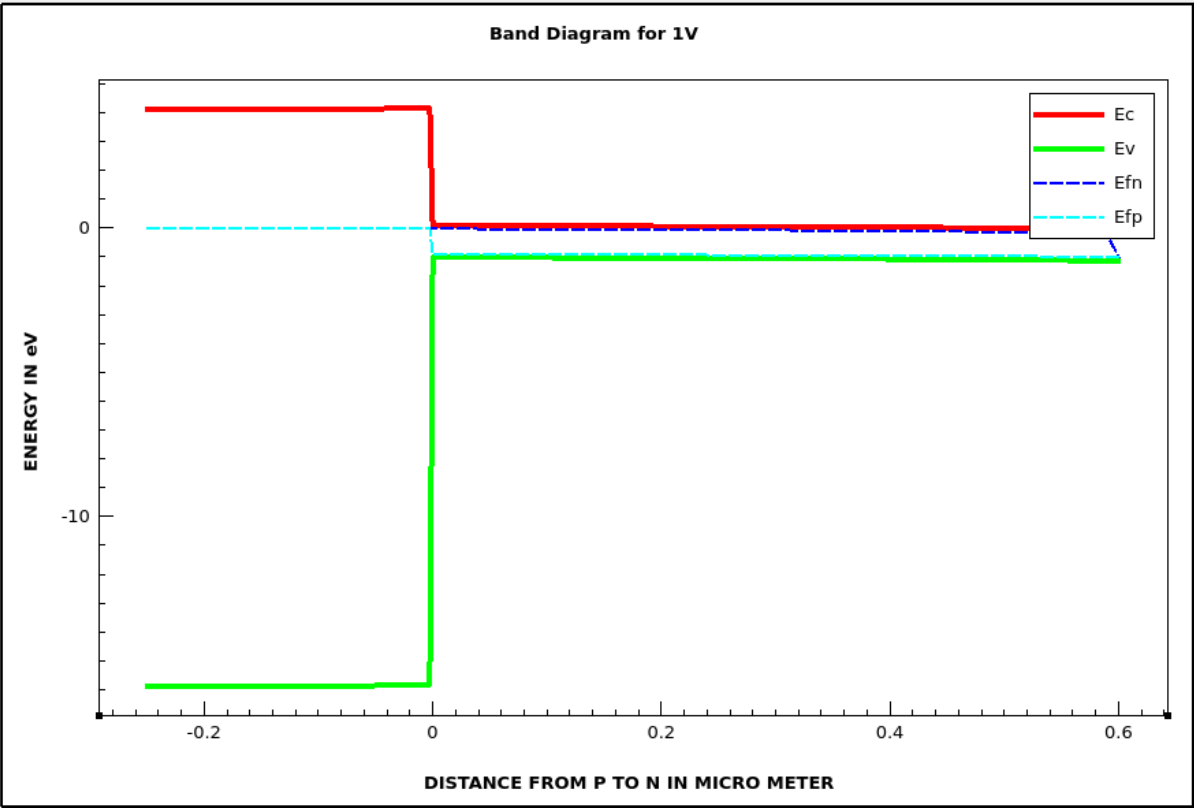
check the nature of this curve. Also plot the CV characteristics in forward bias for 0 to 1 V.

ans :









theoretically =

$$I_0 = q A n_i^2 \left[ \frac{D_p}{L_p N_A} + \frac{D_n}{L_n N_D} \right]$$

When A = total length x width

$$L_p = \sqrt{D_p \tau_p}, L_n = \sqrt{D_n \tau_n}, n_i = 1.5 \times 10^{10}, \mu_n = 1417 \text{ cm}^2/\text{Vsec}$$

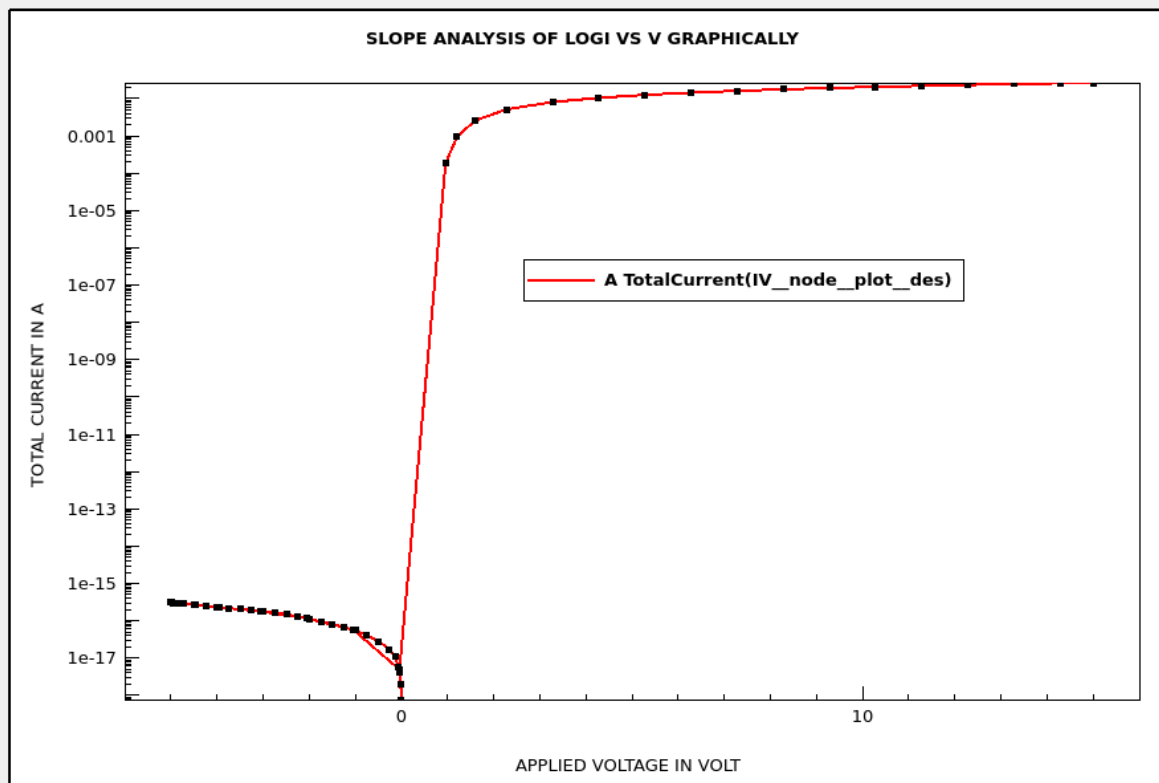
$$\mu_p = 470 \text{ cm}^2/\text{Vsec}, V_T = 0.0258, q = 1.6 \times 10^{-19}, N_D = N_A = 10^{18}$$

$$\tau_p = 0.25 \times 10^{-12}, \tau_n = 0.3 \times 10^{-12}$$

$$I_0 = 5.8 \times 10^{-16} \text{ Amp.}$$

graphically

$$I_0 = 8 \times 10^{-16} \text{ Amp.}$$



Graphically +

Reg ①

pt ①  $(7.49 \times 10^{-1}, 6.27 \times 10^{-8})$  pt ②  $(6.62 \times 10^{-1}, 1.14 \times 10^{-7})$

$$\text{slope} = \frac{y_2 - y_1}{x_2 - x_1} = \frac{1.14 \times 10^{-7} - 6.27 \times 10^{-8}}{6.62 \times 10^{-1} - 7.49 \times 10^{-1}} = \frac{-4.97 \times 10^{-8}}{-0.86 \times 10^{-1}} = 5.77 \times 10^{-7}$$

pt ①  $(9.23 \times 10^{-1}, 1.79 \times 10^{-4})$ , pt ②  $(1.23, 9.2 \times 10^{-4})$

$$\text{slope} = \frac{y_2 - y_1}{x_2 - x_1} = \frac{9.2 \times 10^{-4} - 1.79 \times 10^{-4}}{1.23 - 0.923} = 29.52 \times 10^{-4}$$

Reg ②

pt ①  $(2.3, 5.14 \times 10^{-3})$  pt ②  $(3.30, 7.74 \times 10^{-3})$

$$\text{slope} = \frac{y_2 - y_1}{x_2 - x_1} = \frac{7.74 \times 10^{-3} - 5.14 \times 10^{-3}}{3.3 - 2.3} = 2.6 \times 10^{-3}$$

Reg ③

pt ①  $(6.29, 1.26 \times 10^{-2})$  pt ②  $(7.29, 1.6 \times 10^{-2})$

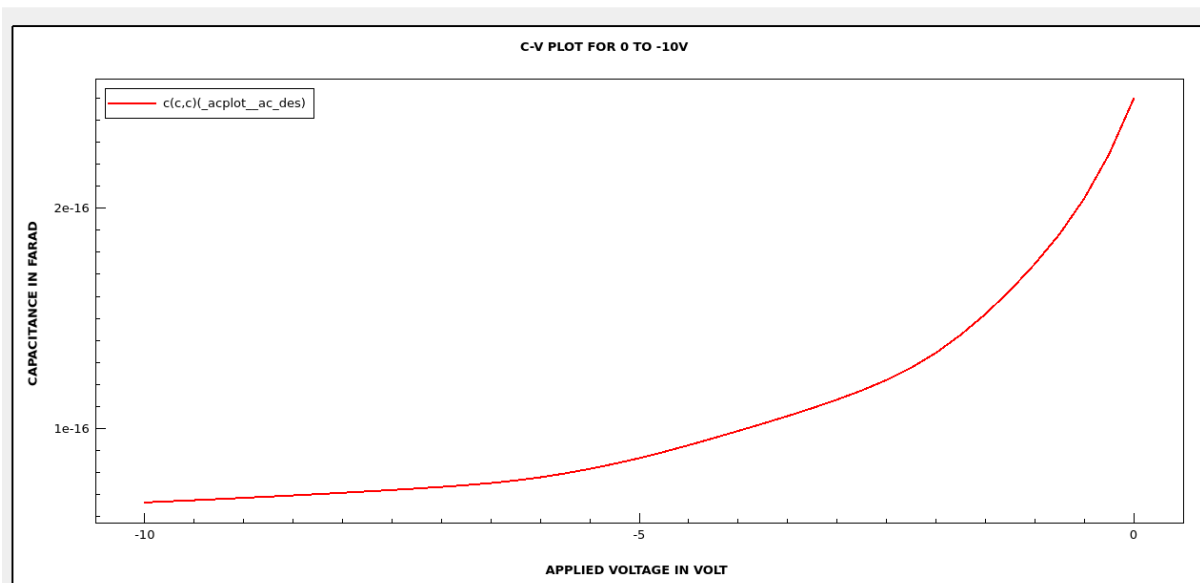
$$\text{slope} = \frac{y_2 - y_1}{x_2 - x_1} = \frac{1.6 \times 10^{-2} - 1.26 \times 10^{-2}}{7.29 - 6.29} = \frac{0.34 \times 10^{-2}}{1} = 0.34 \times 10^{-2}$$

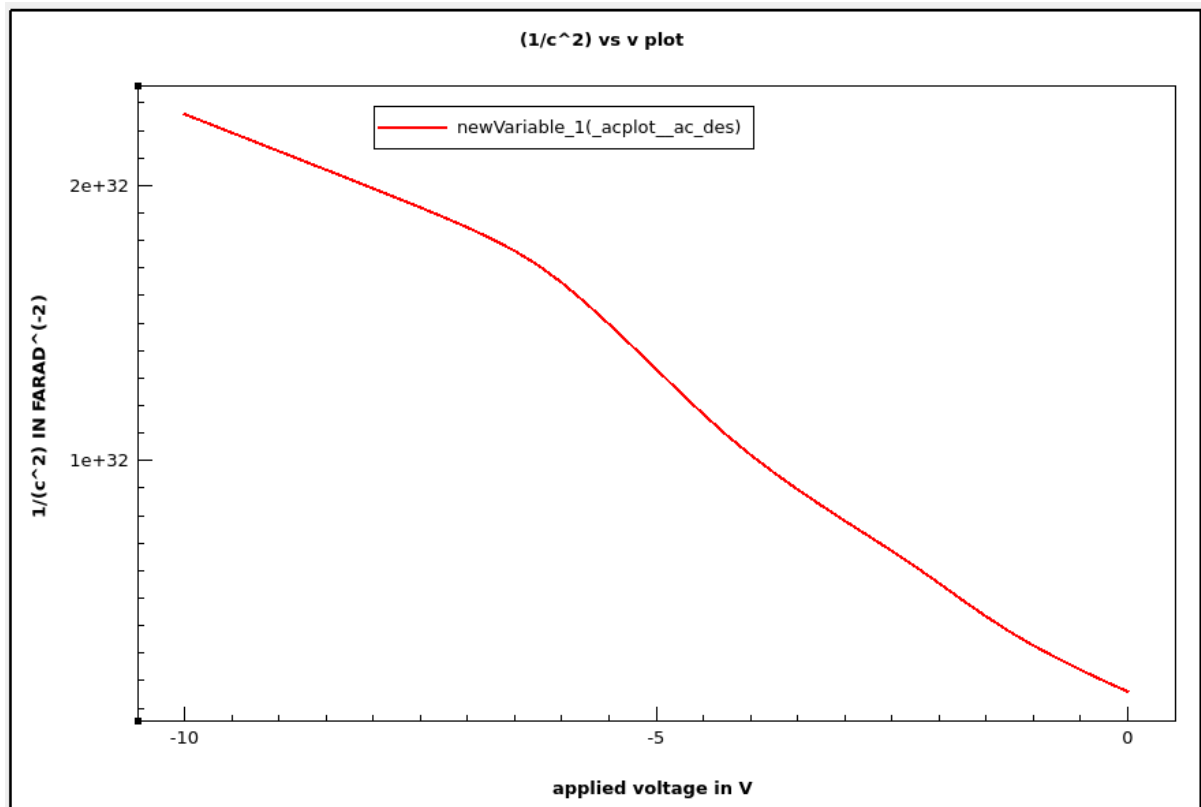
theoretically +

$$I = I_0 (e^{V/V_T} - 1)$$

$\therefore I \approx I_0 e^{V/V_T}$

$$\log I = \log I_0 + V/V_T$$

$$\text{slope} = 1/V_T = 1/0.0258 = 38.759$$




Nature of slope first decreases till around -5 then increases.

